

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:  
David S. Pecora

Serial No.: 09/854,206

Filed: May 11, 2001

For: **ETCH OF SILICON NITRIDE SELECTIVE  
TO SILICON AND SILICON DIOXIDE  
USEFUL DURING THE FORMATION OF A  
SEMICONDUCTOR DEVICE**

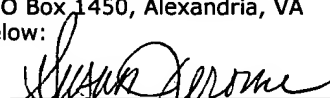
§  
§ Group Art Unit: 1765  
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§ Examiner: Binh X. Tran  
§  
§ Atty. Docket: 00-0737.00/US  
§  
§ Paper No. \*  
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I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail, postage prepaid, in an envelope addressed to: Commissioner for Patents, PO Box 1450, Alexandria, VA 22313-1450, on the date below:

February 5, 2004  
Date

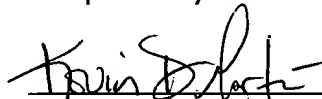
  
Signature

**COMMENTS ON STATEMENT OF REASONS FOR ALLOWANCE**

Applicant submits that each one of the claims of the captioned application is allowable over the cited art for reason of the cited art failing to disclose or suggest the features and/or combination of features as are defined therein. Although applicant acknowledges the Examiner's statement of reasons for allowance as set forth with the Office Action dated July 8, 2003, applicant submits that the reasons for allowance as provided by the Examiner may represent merely a portion of all of the reasons that support the patentability of the claims of the present application without necessarily being exhaustive.

If there are any matters which may be resolved or clarified through a telephone call, the Examiner is cordially invited to contact the undersigned.

Respectfully submitted,



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